2SC5147

Rev.F Mar.-2016

蓝箭电子 BLUE ROCKET ELECTRONICS

DATA SHEET

/ Descriptions

WO0220I ṂṂ Ł NPN Æ Ṁ ч s ǁ ᒣ Silicon NPN transistor in a TO-220F Plastic Package.

/ Features

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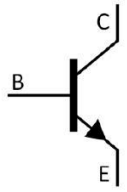
High breakdown voltage, low collector output capacitance, wide SOA.

/ Applications

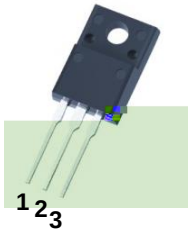
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Ideal for Color TV chroma output and amplification of video signals.

/ Equivalent Circuit



/ Pinning



PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

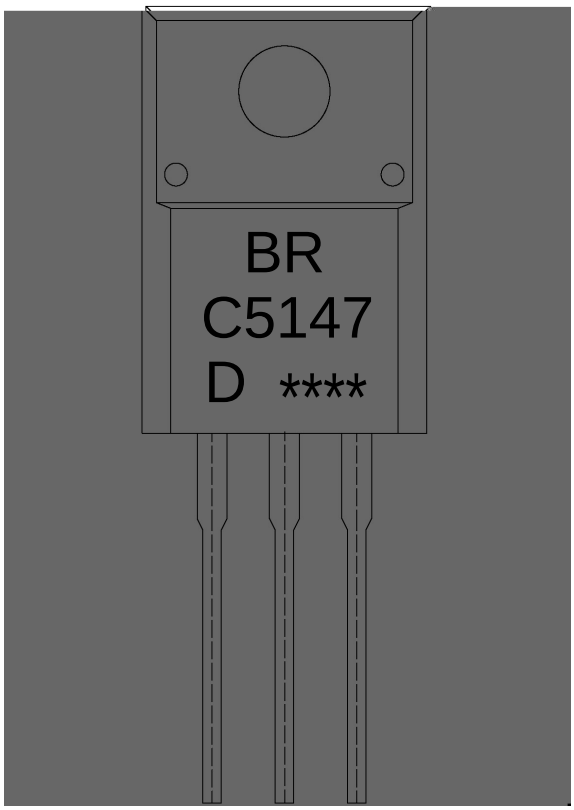
/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	D	E
h_{FE} Range	60 120	100 200

v ̈Ω Parameter	ϒ Symbol	̈Ω Ö Rating	D Ч Unit
Collector to Base Voltage	V_{CBO}	300	V
Collector to Emitter Voltage	V_{CEO}	300	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	100	mA
Collector Power Dissipation	P_C	2.0	W
Collector Power Dissipation	P_C(Tc=25)	10	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

v ̈Ω Parameter	ϒ Symbol	Ш :† ţ Test Conditions	ѡ ņ Ö Min	Ɛ ʒ Ö Typ	ѡ ᶻ Ö Max	D Ч Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=50μA I_E=0	300			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=100μA I_B=0	300			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=50μA I_C=0	5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=200V I_B=0			0.5	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=4.0V I_B=0			0.5	μA
DC Current Gain	h_{FE}	V_{CE}=10V I_C=10mA	60		200	

/ Marking Instructions



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Note:	
BR:	Company Code.
C5147:	Product Type.
D:	h_{FE} Classifications Symbol
****:	Lot No. Code, code change with Lot No.